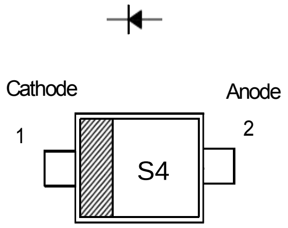
1N5819WT **Surface Mount Schottky Barrier Diodes**

Features

- Low Forward Voltage

MARKING: S4



SOD-523

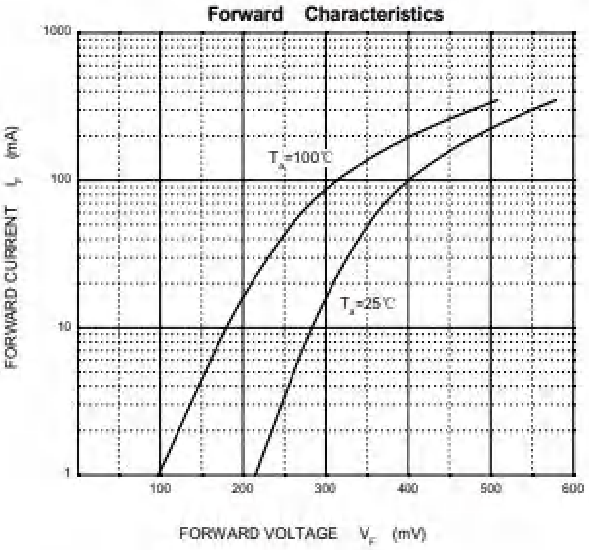
Absolute Maximum Ratings (T_a = 25 °C)

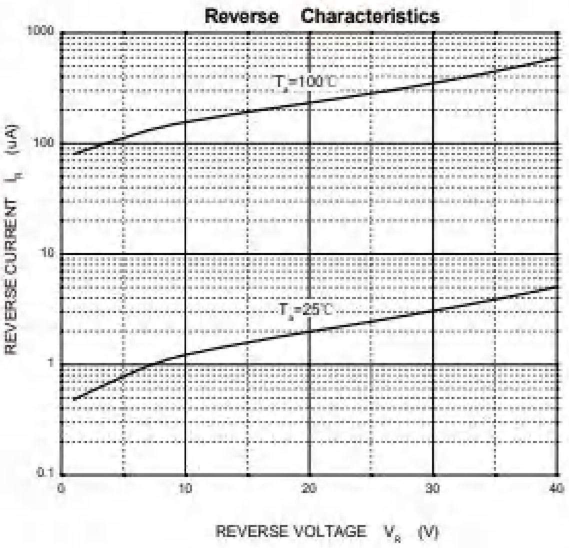
Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Reverse Voltage	V_R	40	V
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s	I_{FSM}	2	A
Power Dissipation	P_{tot}	200	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	°C

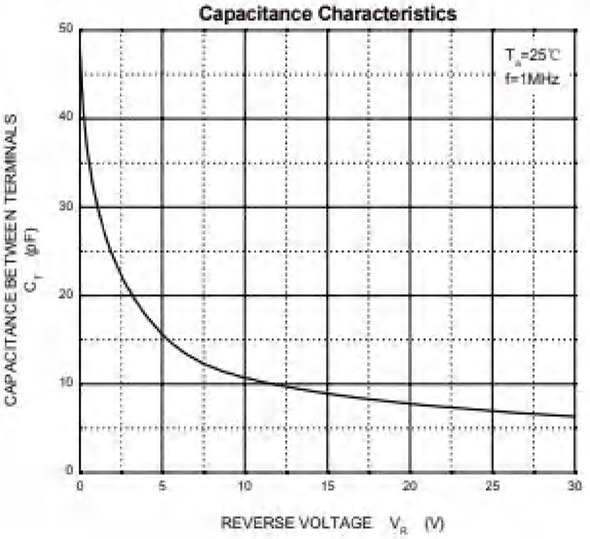
Characteristics at T_a = 25 °C

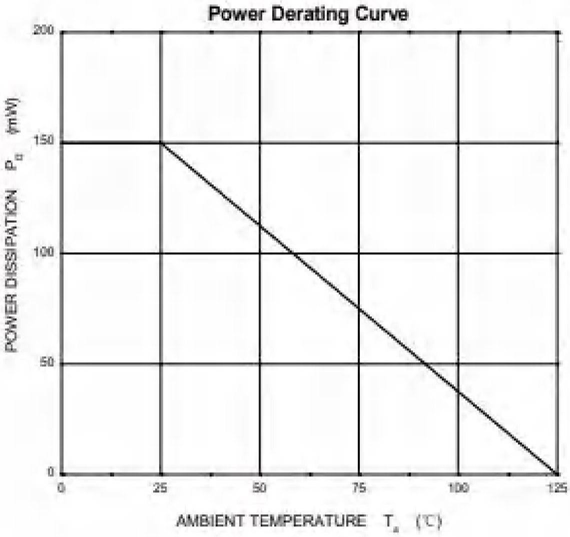
Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I_R=10uA	$V_{(BR)R}$	40	-	-	V
Reverse Leakage Current at V_R =30V	I_R	-	-	5	µA
Forward Voltage at I_F = 20 mA at I_F = 200 mA	V_F	- -	- -	0.37 0.6	V
Total Capacitance at V_R = 0 V, f = 1 MHz	C_T	-	50	-	pF
Reverse Recovery Time at I_F = I_R = 200 mA, I_{rr} = 0.1 I_R, R_L = 100 Ω	t_{rr}	-	10	-	ns

Typical Characteristics



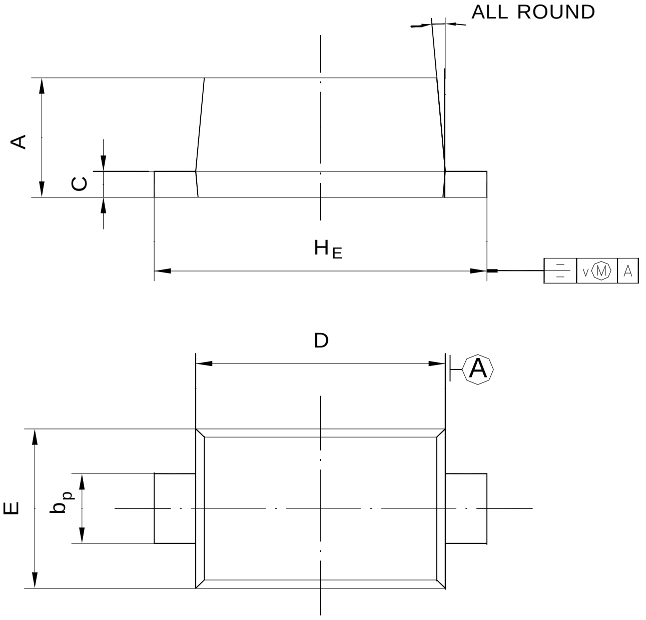






PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.68 0.58	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°